

REPLACEMENT MATERIALS PROCESSES FOR FORMING CROSS POINT MEMORY

ABSTRACT

Methods of forming memory cells comprising phase change and/or chalcogenide materials are disclosed. In one aspect, the method includes providing a lower line stack extending in a first direction, the lower line stack comprising a sacrificial line over a lower conductive line. The method further includes forming a chalcogenide line extending in the first, direction by selectively removing the sacrificial material of the sacrificial line and replacing the sacrificial line with chalcogenide material.

Figure 3E